

ABSTRACT OF THE DISCLOSURE

A first film is formed on a semiconductor substrate, the first film being made of material having a different etching resistance from silicon carbide.

A second film of hydrogenated silicon carbide is formed on the first film. A resist

5 film with an opening is formed on the second film. By using the resist mask as

an etching mask, the second film is dry-etched by using mixture gas of

fluorocarbon gas added with at least one of SF_6 and NF_3 . The first film is

etched by using the second film as a mask. A semiconductor device

manufacture method is provided which utilizes a process capable of easily

10 removing an etching stopper film or hard mask made of SiC .

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